

Nonvolatile, I²C Compatible 256-Position, Digital Potentiometer

Preliminary Technical Data

FEATURES

Nonvolatile memoy maintains wiper settings 256-position Compact MSOP-10 (3 mm × 4.9 mm) package I²C[®] compatible interface VLOGIC pin provides increased interface flexibility. End-to-end resistance 5 k Ω , 10 k Ω , 50 k Ω , 100 k Ω **Resistance tolerance stored in EEMEM(0.1% accuracy)** Power On EEMEM Refresh Time < 1ms Software write protect command Tri-state address decode pins AD0 and AD1 100-year typical data retention at 55°C Wide operating temperature -40°C to +85°C +3V to +5V single-supply

APPLICATIONS

LCD panel V_{COM} adjustment LCD panel brightness and contrast control Mechanical potentiometer replacement in new designs Programmable power supplies **RF** amplifier biasing Automotive electronics adjustment Gain control and offset adjustment Low resolution DAC replacement **Electronics level settings**

GENERAL OVERVIEW

The AD5259 provides a compact nonvolatile 3 mm \times 4.9 mm packaged solution for 256-position adjustment applications. These devices perform the same electronic adjustment function as mechanical potentiometers or variable resistors, with enhanced resolution and solid-state reliability.

The wiper settings are controllable through an I²C compatible digital interface, which can also be used to read back the wiper register and EEMEM content. Resistor tolerance is also stored within EEMEM and can be used to provide an end-to-end tolerance accuracy of 0.1%. In order to provide added security, command bits are available to place the part into a write protect mode in which data can not be written to the EEMEM register.

In addition, a separate VLOGIC pin provides the user with increased interface flexibility. For users who need multiple

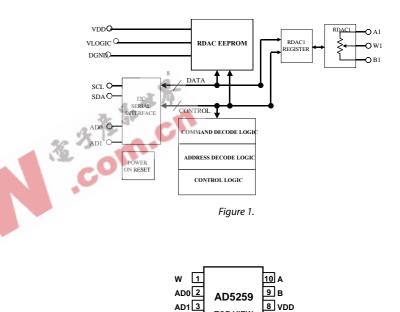
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AD5259

parts on one bus, address bits AD0 and AD1 allow up to nine devices on the same bus.

FUNCTIONAL BLOCK DIAGRAMS



SDA4

SCL 5

Figure 3. Pinout.

TOP VIEW

(Not to Scale)

7 GND

6 VLOGIC

Note

The terms digital potentiometer, VR, and RDAC are used interchangeably.

Purchase of licensed I²C components of Analog Devices or one of its sublicensed Associated Companies conveys a license for the purchaser under the Philips I²C Patent Rights to use these components in an I²C system, provided that the system conforms to the I²C Standard Specification as defined by Philips.

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REVISION HISTORY

Revision 0: Initial Version

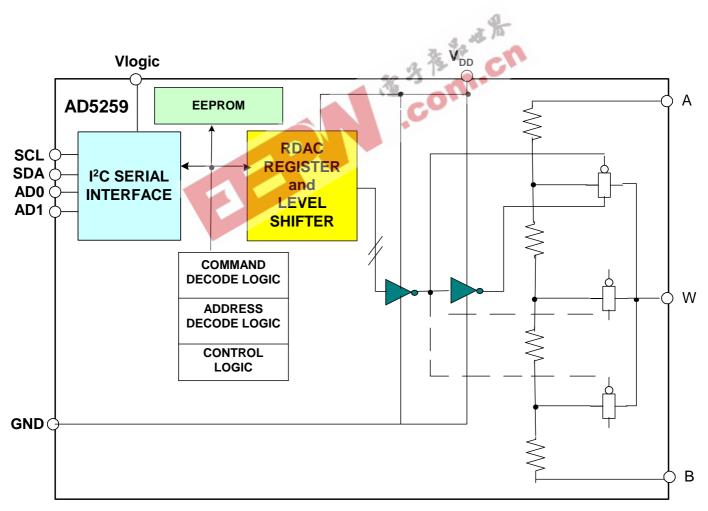


Figure 3. Block diagram showing level shifters

ELECTRICAL CHARACTERISTICS—5 k $\Omega,$ 10 k $\Omega,$ 50 k $\Omega,$ 100 k Ω versions

 $(V_{DD} = 5 \text{ V} \pm 10\%, \text{ or } 3 \text{ V} \pm 10\%; V_A = V_{DD}; V_B = 0 \text{ V}; -40^{\circ}\text{C} < T_A < +85^{\circ}\text{C}; \text{ unless otherwise noted.})$

Parameter	Symbol	Conditions	Min		Max	Unit
DC CHARACTERISTICS—RHEOSTAT MODE						
Resistor Differential Nonlinearity	R-DNL	R _{WB} , V _A = no connect	-1	±0.1	+1	LSB
Resistor Integral Nonlinearity	R-INL	R _{WB} , V _A = no connect	-2	±0.25	+2	LSB
Nominal Resistor Tolerance	ΔR _{AB}	$T_A = 25^{\circ}C$	-30		+30	%
Resistance Temperature Coefficient	$\Delta R_{AB} / \Delta T$	V _{AB} = V _{DD} , Wiper = no connect		650		ppm/°0
Rwb	RwB	Code = 0x00		50	120	Ω
DC CHARACTERISTICS—POTENTIOMETER DIVIDER	RMODE	·				
Differential Nonlinearity	DNL		-1	±0.1	+1	LSB
Integral Nonlinearity	INL		-1	±0.3	+1	LSB
Voltage Divider Temperature Coefficient	$\Delta V_W / \Delta T$	Code = 0x80		30		ppm/°0
Full-Scale Error	Vwfse	Code = 0xFF	-3	-1	0	LSB
Zero-Scale Error	V _{WZSE}	Code = 0x00	0	1	3	LSB
RESISTOR TERMINALS		A. 45 P				
Voltage Range	V _{A,B,W}	32 34	Vss		V _{DD}	V
Capacitance A, B	C _{A,B}	f = 1 MHz, measured to GND, Code = $0x80$		45		pF
Capacitance W	Cw	f = 1 MHz, measured to GND, Code = 0x80		60		pF
Common-Mode Leakage	Ісм	$V_A = V_B = V_{DD}/2$		1		nA
DIGITAL INPUTS AND OUTPUTS						
Input Logic High	VIH		$0.7 \times V_{\text{L}}$		V _L +0.5	V
Input Logic Low	VIL		-0.5		$0.3 \times V_{L}$	V
Input Current	la.	$V_{IN} = 0 V \text{ or } 5 V$			±1	μA
Input Capacitance	CIL			5		рF
POWER SUPPLIES						
Power Supply Range	V _{DD}		2.7		5.5	V
Positive Supply Current	IDD	$V_{IH} = 5 V \text{ or } V_{IL} = 0 V$			1	μA
Logic Supply(must match logic levels)	VLOGIC		2.7		V _{DD}	
Programming Mode Current(EEMEM)		$V_{IH} = 5 V \text{ or } V_{IL} = 0 V$		35		mA
Power Dissipation	P _{DISS}			18	50	μW
Power Supply Sensitivity	PSS	$V_{DD} = +5 V \pm 10\%$, Code = Midscale		±0.02	±0.05	%/%
DYNAMIC CHARACTERISTICS						
Bandwidth –3dB	BW	$\begin{split} R_{AB} &= 5k\Omega/\ 10\ k\Omega/50\ k\Omega/100\\ k\Omega,\ Code &= 0x80 \end{split}$		2000/600/ 100/40		kHz
Total Harmonic Distortion	THDw	$V_A = 1 V rms$, $V_B = 0 V$, f = 1 kHz, $R_{AB} = 10 k\Omega$		0.1		%
V_W Settling Time (1kΩ/10 kΩ/50 kΩ/100 kΩ)	ts	$V_A = 5 V$, $V_B = 0 V$, ±1 LSB error band		2		μs
Resistor Noise Voltage Density	en_wb	$R_{WB} = 5 k\Omega$, $RS = 0$		9		nV/√H

TIMING CHARACTERISTICS—5 kΩ, 10 kΩ, 50 kΩ, 100 kΩ VERSIONS

 $(V_{DD} = +5V \pm 10\%, \text{ or } +3V \pm 10\%; V_A = V_{DD}; V_B = 0 \text{ V}; -40^{\circ}\text{C} < T_A < +85^{\circ}\text{C}; \text{ unless otherwise noted.})$

Table 2.						
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
I ² C INTERFACE TIMING CHARACTERISTICS ¹ (Specificat	tions Apply 1	to All Parts)				
SCL Clock Frequency	f _{SCL}		0		400	kHz
$t_{\mbox{\scriptsize BUF}}$ Bus Free Time between STOP and START	t1		1.3			μs
$t_{HD;STA}$ Hold Time (Repeated START)	t ₂	After this period, the first clock pulse is generated.	0.6			μs
tLOW Low Period of SCL Clock	t ₃		1.3			μs
thigh High Period of SCL Clock	t4		0.6			μs
tsu;sta Setup Time for Repeated START Condition	t₅		0.6			μs
thd;dat Data Hold Time	t ₆		0		0.9	μs
tsu;dat Data Setup Time	t7		100			ns
t _F Fall Time of Both SDA and SCL Signals	t ₈				300	ns
$t_{\mbox{\tiny R}}$ Rise Time of Both SDA and SCL Signals	t9				300	ns
tsu;sto Setup Time for STOP Condition	t 10	- 8-	0.6			μs

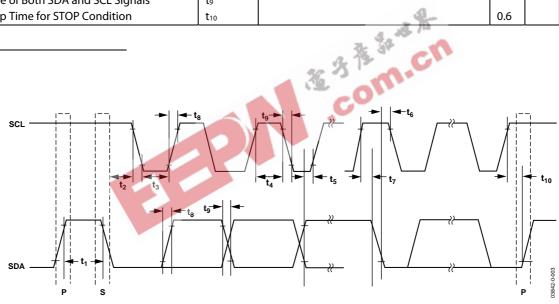


Figure 4. I²C Interface Timing Diagram

Preliminary Technical Data

I²C INTERFACE

Table 3. Generic Interface Format

	S	Device Address* (7-bit) R	R/W	SA	C2	C1	C0	A4	A3	A2	A1	A0	SA	D7	D6	D5	D4	D3	D2	D1	D0	SA	Р
Ī		Slave Address Byte					Ins	truct	ion B	yte							Data	Byte					

Table 4. Device Address Lookup* (Note that AD1 and AD0 are tri-state address pins)

Device Address	AD1	AD0	S = Start Condition
0011000	0	0	
0011001	NC	0	P = Stop Condition
0011010	1	0	SA = Slave Acknowledge
0101001	0	NC	MA Master Advandadas
0101010	NC	NC	MA = Master Acknowledge
0101011	1	NC	NA = No Acknowledge
1001100	0	1	X = Don't Care
1001101	NC	1	X = Dont Care
1001110	1	1	$\overline{W} = Write$
			R = Read

Table 5. RDAC-to-EEMEM Interface Command Descriptions

C2	C1	C0	Command Description
0	0	0	Operation between I ² C and RDAC
0	0	1	Operation between I ² C and EEPROM
0	1	0	Operation between I ² C and WP register
1	0	0	NOP
1	0	1	Restore EEPROM to RDAC
1	1	0	Store RDAC to EEPROM

Write Modes

Table 6. Writing to RDAC register

																			-			
	Device Address*																					
S	(7-bit)	0	SA	0	0	0	0	0	0	0	0	SA	D7	D6	D5	D4	D3	D2	D1	D0	SA	Р
	Slave Address Byte					Inst	truct	ion B	yte							Data	Byte					

Table 7. Writing to EEPROM register

c	Device Address*		6.4	0	0	1	0	0	0	0	0	6.4	57		D5		50	50	D1		C A	D
2	(7-bit)	0	SA	0	0	1	0	0	0	0	0	SA	D7	D6	05	D4	D3	D2	D1	D0	SA	Р
	Slave Address Byte					Ins	truct	ion B	yte							Data	Byte					

Table 8. Activating Software Write Protect

_	0		-									r										
	Device Address*																					
S	(7-bit)	0	SA	0	1	0	0	0	0	0	0	SA	0	0	0	0	0	0	0	WP	SA	Р
	Slave Address Byte					Ins	truct	ion B	yte					The		Data	Byte					
Sto	Slave Address Byte Instruction Byte Data Byte																					
Table	e 9. Storing RDAC value to EEH	PRO	М																			
	Device Address*																					

Store/Restore Modes

Table 9. Storing RDAC value to EEPROM

_	0											1. Contract (1. Contract)	
	Device Address*												
S	(7-bit)	0	SA	1	1	0	0	0	0	0	0	SA	Ρ
	Slave Address Byte					nsti	ruct	ion	Byte	2			

Table 10. Restoring EEPROM to RDAC

	Device Address*												
S	(7-bit)	0	SA	1	0	1	0	0	0	0	0	SA	Ρ
	Slave Address Byte				I	nstr	uct	ion	Byte	j			

- S = Start Condition
- P = Stop Condition
- SA = Slave Acknowledge
- MA = Master Acknowledge
- NA = No Acknowledge
- X = Don't Care

 $\overline{W} = Write$

R = Read

Read Modes

Table 11. Traditional Read back of RDAC Register value												
	evice Address*							Device Address*		~		
S S	(7-bit) lave Address Byte	0 SA		0 0 ructior) SA	5	(7-bit) Slave Address Byte	1	SA D7	D6 D5 D4 D3 D2 D1 D0 NA F Read Back Data	Ť
	· · · · · · · · · · · · · · · · · · ·		-		- /		•					1
T												
Repeat start												
Table 12. Traditional Read back of stored EEPROM value Device Address* Device Address*												
S	(7-bit)	0 SA	0 0 1	0 0) SA	S	(7-bit)	1	SA D7	D6 D5 D4 D3 D2 D1 D0 NA F	2
S	lave Address Byte		Inst	ructior	n Byte			Slave Address Byte			Read Back Data	Ι
Slave Address byte Instruction byte Slave Address byte Read back Data Table 13. Traditional Read back of Tolerance Repeat start Image: Consecutively Device Device Device												
Table 13. Traditional Read back of Tolerance												
	ecutively						1	2011	_			_
Ad	evice dress* 7-bit) 0 SA 0	0 1 1	1 1 1 1 0	SA S	Device Address (7-bit)			D7 D6 D5 D4 D3 D2 D1	D		D6 D5 D4 D3 D2 D1 D0 NA I	Р
Slav	ve Address Byte I	nstruc	tion Byte		Slave Add Byte	lress		Sign + Integer Byte			Decimal Byte	
ii. Indi	vidually			Repeat	start							
S (7	evice dress* 0 SA 0 7-bit) 0 SA 0	0 1 1	1 1 1 0	SA S	Device Address (7-bit) Slave Add	1	SA	D7 D6 D5 D4 D3 D2 D1 Sign + Integer Byte	D 0 I	NA P		
	Byte I	nstruc	tion Byte		Byte			5 5 7				
\uparrow												
Repeat start												
Ad S (7	evice dress* 7-bit) 0 SA 0	0 1 1	1 1 1 1	SA S	Device Address (7-bit)	1	SA	D7 D6 D5 D4 D3 D2 D1	D 0	NA P		
Slav	ve Address Byte I	nstruc	tion Byte		Slave Ado Byte	lress		Decimal Byte				
				↑							_	

Repeat start

Note: Read modes above are referred to as traditional because the first two bytes for all three cases are "dummy" bytes which function to place the pointer towards the correct register. This is the reason for the Repeat Start. In theory, this step can be avoided if the user is interested in reading a register that was previously written to. For example, if the EEPROM was just written to, then the user can skip the

two dummy bytes and proceed directly to the "Slave Address Byte" which would be followed by the "Read Back Data".

Calculating R_{AB} Tolerance Stored in Read-Only Memory

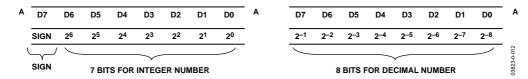


Figure 5. Format of Stored Tolerance in Sign Magnitude Format with Bit Position Descriptions. (Unit is percent. Only data bytes are shown.)

The AD5259 features a patented R_{AB} tolerance storage in the nonvolatile memory. The tolerance is stored in the memory during factory production and can be read by users at any time. The knowledge of stored tolerance allows users to calculate R_{AB} accurately. This feature is valuable for precision, rheostat mode, and open-loop applications where knowledge of absolute resistance is critical.

The stored tolerance resides in the read-only memory, and is expressed as a percentage. The tolerance is stored in two memory locations in sign magnitude binary form(see Figure 5). The two EEMEM address bytes are 11110(sign+integer) and 11111 (decimal number). The two bytes can be accessed individually in two separate commands(see Table 13ii). Alternatively, in order to allow read back of the first byte followed by the second byte in one command(see Table 13i), the memory pointer will automatically increment from the first to the second EEMEM locations(increments from 11110 to 11111) if read consecutively.

In the first memory location, the MSB is designated for the sign (0 = + and 1 = -) and the 7 LSBs are designated for the integer portion of the tolerance. In the second memory location, all eight data bits are designated for the decimal portion of tolerance. For example, if the rated R_{AB} = 10 k Ω and the data readback from Address 11110 shows 0001 1100 and Address 11111 shows 0000 1111, then the tolerance can be calculated as

MSB: 0 = + Next 7 MSB: 001 1100 = 28 8 LSB: 0000 1111 = $15 \times 2^{-8} = 0.06$ Tolerance = +28.06% and therefore R_{AB_ACTUAL} = 12.806 k Ω

EEMEM Write-Acknowledge Polling

After each write operation to the EEMEM registers, an internal write cycle begins. The I²C interface of the device is disabled. To determine if the internal write cycle is complete and the I²C interface is enabled, interface polling can be executed. I²C interface polling can be conducted by sending a start condition followed by the slave address + the write bit. If the I²C interface responds with an ACK, the write cycle is complete and the interface is ready to proceed with further operations. Other-wise, I²C interface polling can be repeated until it succeeds.

I²C COMPATIBLE 2-WIRE SERIAL BUS

1. The master initiates data transfer by establishing a START condition, which is when a high-to-low transition on the SDA line occurs while SCL is high (see Figure 4). The following byte is the Slave Address Byte, which consists of the slave address followed by an R/\overline{W} bit (this bit determines whether data is read from or written to the slave device).

The AD5259 has two tri-state configurable address bits, AD0 and AD1 (see Table 4). The slave whose address corresponds to the transmitted address responds by pulling the SDA line low during the ninth clock pulse (this is termed the acknowledge bit). At this stage, all other devices on the bus remain idle while the selected device waits for data to be written to or read from its serial register. If the R/W bit is high, the master reads from the slave device. If the R/W bit is low, the master writes to the slave device.

 Writing: In the write mode, the last bit(R/W) of the Address Byte is logic low. The second byte is the Instruction Byte. The first 3 bits of the Instruction Byte are the command bits(see Table 5). The final 5 bits indicate which EEMEM location the pointer moves to. The user must choose whether to write to the RDAC register, EEMEM register, or activate the software write protect(see Tables 6-8).

The final byte is the Data Byte MSB first. In the case of the write protect mode, data is not being stored. Rather, a logic high in the LSB will enable write protect and a logic low will disable write protect.

Storing/Restoring: In this mode, only two bytes are necessary; Address and Instruction Bytes. The last bit (R/W) of the Address Byte is logic low. The first 3 bits of the Instruction Byte are the command bits(see Table 5). The two choices are transfer data from RDAC to EEMEM(Store) or from EEMEM to RDAC(Restore). The final 5 bits are all zeros(see Tables 9-10).

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- 4. **Reading:** Assuming the register of interest was not just written to, it is necessary to write a dummy Address and Instruction Byte. The Instruction Byte will vary depending on whether the data that is wanted is the RDAC register, EEMEM register, or Tolerance register(see Tables 11-13). The Tolerance register can be read back consecutively(Table 13i) or individually(Table13ii). Refer to page 8 for detailed information on the interpretation of the tolerance bytes. After the dummy Address and Instruction Bytes are sent, a repeat start is necessary. After the repeat start, another Address Byte is needed except this time, the R/\overline{W} bit is logic **high**. Following this Address Byte is the Read Back Byte containing the information requested in the Instruction Byte.
- 5. After all data bits have been read or written, a STOP condition is established by the master. A STOP condition is defined as a low-to-high transition on the SDA line while SCL is high. In write mode, the master pulls the SDA line high during the 10th clock pulse to establish a STOP condition (see Figure 6). In read mode, the master issues a No Acknowledge for the ninth clock pulse (i.e., the SDA line low before the 10th clock pulse, and then raises SDA high to establish a STOP condition (see Figure 7).

A repeated write function gives the user flexibility to update the RDAC output a number of times after addressing and instructing the part only once. For example, after the RDAC has acknowledged its Slave Address and Instruction Bytes in the write mode, the RDAC output is updated on each successive byte. If different instructions are needed, the write/read mode has to start again with a new Slave Address, Instruction, and Data Byte. Similarly, a repeated read function of the RDAC is also allowed.

DISPLAY APPLICATIONS

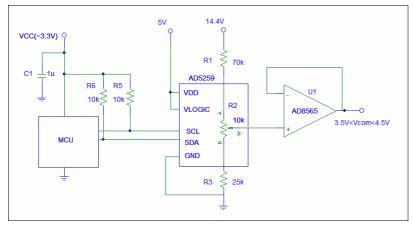


Figure 1. V_{COM} adjustment application assuming that a +5V supply is available. In this case, V_{DD} and V_{LOGIC} would be tied together.

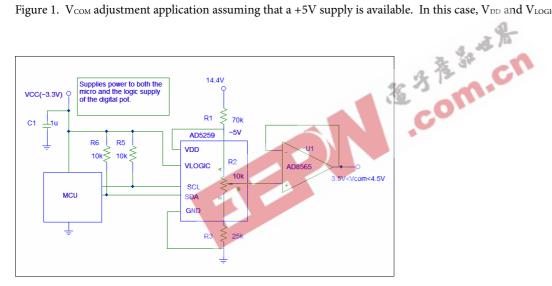


Figure 2. This circuit demonstrates the flexibility of a V_{LOGIC} pin when a separate supply is not available for V_{DD}. V_{DD} can be tapped off the +14.4V where it is resistor divided down to approximately ~5V. VLOGIC can then be taken off the same supply that powers the MCU's logic levels. Now, the 35 mA programming current will be drawn by VLOGIC, and VDD will only draw microamps of supply current used to bias up the internal switches in the digital potentiometer's internal resistor string.

ABSOLUTE MAXIMUM RATINGS¹

 $(T_A = +25^{\circ}C, unless otherwise noted.)$

Table 4

Parameter	Value		
V _{DD} to GND	–0.3 V to +7 V		
V _A , V _B , V _W to GND	V _{SS} -0.3V, V _{DD} +0.3V		
Imax			
Pulsed ¹	±20 mA		
Continuous	±5 mA		
Digital Inputs and Output Voltage to GND	0 V to +7 V		
Operating Temperature Range	-40°C to +85°C		
Maximum Junction Temperature (T _{JMAX})	150°C		
Storage Temperature	–65°C to +150°C		
Lead Temperature (Soldering, 10 sec)	300°C		
Thermal Resistance ² θ _{JA} : MSOP-10	200°C/W		
NOTEC			

NOTES

透牙港。「 ¹Maximum terminal current is bounded by the maximum current handling of the switches, maximum power dissipation of the package, and maximum applied voltage across any two of the A, B, and W terminals at a given resistance.

² Package power dissipation = $(T_{JMAX} - T_A)/\theta_{JA}$.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

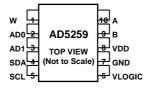


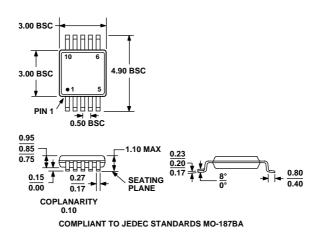
Figure 2. AD5172 Pin Configuration

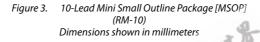
Table 5. AD5259 Pin Function Descriptions

Pin	Mnemonic	Description
1	W	W Terminal. $GND \le V_W \le V_{DD}$.
2	ADO	Programmable Tri-State Address Bit 0 for Multiple Package Decoding.
3	AD1	Programmable Tri-State Address Bit 1 for Multiple Package Decoding.
4	SDA	Serial Data Input/Output.
5	SCL	Serial Clock Input. Positive edge triggered. 💦 💰 🏴
6	VLOGIC	Logic power supply. Digital Ground. Positive Power Supply.
7	GND	Digital Ground.
8	VDD	Positive Power Supply. 🔁 🌾 🕐
9	В	B Terminal. GND $\leq V_{B} \leq V_{DD}$.
10	А	A Terminal. GND $\leq V_A \leq V_{DD}$.

Preliminary Technical Data

Outline Dimensions





ORDERING GUIDE

Figure 3. 10-Lead Mini Small Outline Package [MSOP] (RM-10)										
Dimensions shown in millimeters										
	ORDERING GUIDE									
	2 1º - C									
ORDERING GUIDE										
Model	R _{AB} (Ω)	Temperature	Package Description	Package Option	Branding					
AD5259BRMZ51	5k	-40°C to +85°C	MSOP-10	RM-10	D4P					
AD5259BRMZ5-RL7 ¹	5k	-40°C to +85°C	MSOP-10	RM-10	D4P					
AD5259BRMZ10 ¹	10k	-40°C to +85°C	MSOP-10	RM-10	D4Q					
AD5259BRMZ10-RL71	10k	-40°C to +85°C	MSOP-10	RM-10	D4Q					
AD5259BRMZ501	50k	-40°C to +85°C	MSOP-10	RM-10	D4R					
AD5259BRMZ50-RL71	50k	-40°C to +85°C	MSOP-10	RM-10	D4R					
AD5259BRMZ100 ¹	100k	-40°C to +85°C	MSOP-10	RM-10	D4S					
AD5259BRMZ100-RL7 ¹	100k	-40°C to +85°C	MSOP-10	RM-10	D4S					

 1 Z = Pb-free part.

ESD CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although this product features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



NOTES



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